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2-Input NAND Schmitt-Trigger with Open Drain Output

MC74VHC1G135

The MC74VHC1G135 is a single gate CMOS Schmitt NAND trigger with an open drain output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffered 3−state output which provides high noise immunity and stable output.

The input structures provide protection when voltages up to 5.5 V are applied, regardless of the supply voltage. This allows the device to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when V_{CC} = 0 V and when the output voltage exceeds V_{CC}. These input and output structures help prevent device destruction caused by supply voltage − input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- Designed for 2.0 V to 5.5 V V_{CC} Operation
- 4.9 ns t_{PD} at 5 V (typ)
- Inputs/Outputs Over−Voltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Source/Sink 8 mA at 3.0 V
- Available in SC−88A, SC−74A, TSOP−5, SOT−553, SOT−953 and UDFN6 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

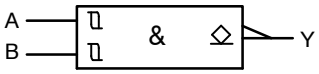

Figure 1. Logic Symbol

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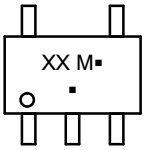
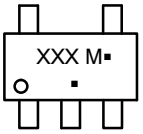
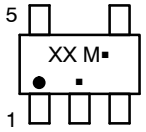
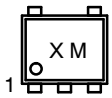
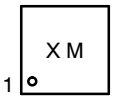
MARKING DIAGRAMS

	**SC−88A DF SUFFIX CASE 419A**	
	**SC−74A DBV SUFFIX CASE 318BQ**	
	**TSOP−5 DT SUFFIX CASE 483**	
	**SOT−553 XV5 SUFFIX CASE 463B**	
	**SOT−953 P5 SUFFIX CASE 527AE**	
	**UDFN6 1.45 x 1.0 CASE 517AQ**	
	**UDFN6 1.0 x 1.0 CASE 517BX**	

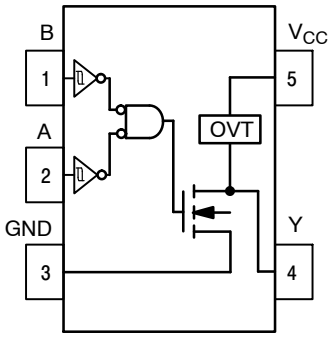
XX = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

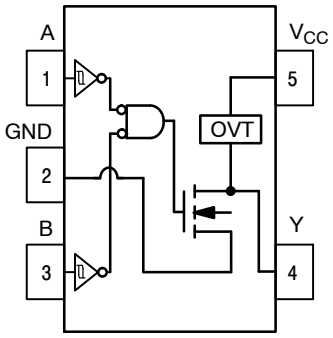
*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

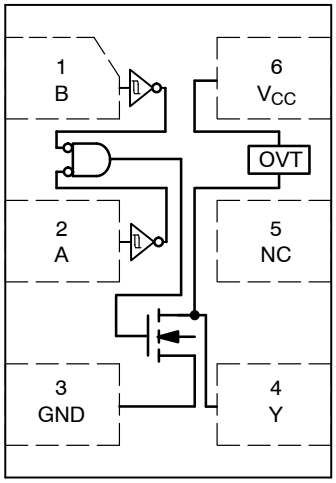
See detailed ordering, marking and shipping information in the package dimensions section on page 7 of this data sheet.



(SC−88A/SOT−553/ TSOP−5/ SC−74A)



SOT−953



UDFN6

Figure 2. Pinout (Top View)

PIN ASSIGNMENT
(SC−88A/SOT−553/ TSOP−5/SC−74A)

Pin	Function
1	B
2	A
3	GND
4	Y
5	V_{CC}

PIN ASSIGNMENT (SOT−953)

Pin	Function
1	A
2	GND
3	B
4	Y
5	V_{CC}

PIN ASSIGNMENT (UDFN)

Pin	Function
1	B
2	A
3	GND
4	Y
5	NC
6	V_{CC}

FUNCTION TABLE

Input		Output
A	**B**	**Y**
L	L	Z
L	H	Z
H	L	Z
H	H	L

MAXIMUM RATINGS

Symbol	Characteristics		Value	Unit
V_{CC}	DC Supply Voltage	TSOP−5, SC−88A (NLV) SC−74A, SC−88A, UDFN6, SOT−553, SOT−953	−0.5 to +7.0 −0.5 to +6.5	V
V_{IN}	DC Input Voltage	TSOP−5, SC−88A (NLV) SC−74A, SC−88A, UDFN6, SOT−553, SOT−953	−0.5 to +7.0 −0.5 to +6.5	V
V_{OUT}	DC Output Voltage TSOP−5, SC−88A (NLV)	Active−Mode (High or Low State) Tri−State Mode (Note 1) Power−Down Mode (V_{CC} = 0 V)	−0.5 to V_{CC} + 0.5 −0.5 to +7.0 −0.5 to +7.0	V
	DC Output Voltage SC−74A, SC−88A, UDFN6, SOT−553, SOT−953	Active−Mode (High or Low State) Tri−State Mode (Note 1) Power−Down Mode (V_{CC} = 0 V)	−0.5 to V_{CC} + 0.5 −0.5 to +6.5 −0.5 to +6.5	V
I_{IK}	DC Input Diode Current	V_{IN} < GND	−20	mA
I_{OK}	DC Output Diode Current	V_{OUT} < GND	−20	mA
I_{OUT}	DC Output Source/Sink Current		±25	mA
I_{CC} or I_{GND}	DC Supply Current per Supply Pin or Ground Pin		±50	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 secs		260	°C
T_J	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 2)	SC−88A SC−74A SOT−553 SOT−953 UDFN6	377 320 324 254 154	°C/W
P_D	Power Dissipation in Still Air	SC−88A SC−74A SOT−553 SOT−953 UDFN6	332 390 386 491 812	mW
MSL	Moisture Sensitivity		Level 1	−
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	−
V_{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
$I_{Latchup}$	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri−stated.
2. Measured with minimum pad spacing on an FR4 board, using 10mm−by−1inch, 2 ounce copper trace no air flow per JESD51−7.
3. HBM tested to ANSI/ESDA/JEDEC JS−001−2017. CDM tested to EIA/JESD22−C101−F. JEDEC recommends that ESD qualification to EIA/JESD22−A115−A (Machine Model) be discontinued per JEDEC/JEP172A.
4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		2.0	5.5	V
V_{IN}	DC Input Voltage		0	5.5	V
V_{OUT}	DC Output Voltage	TSOP−5, SC−88A (NLV)	0	V_{CC}	V
	DC Output Voltage	SC−74A, SC−88A, UDFN6, SOT−553, SOT−953 Active−Mode (High or Low State) Tri−State Mode (Note 1) Power−Down Mode (V_{CC} = 0 V)	 0 0 0	 V_{CC} 5.5 5.5	
T_A	Operating Temperature Range		−55	+125	°C
t_r , t_f	Input Rise and Fall Time	TSOP−5, SC−88A (NLV) V_{CC} = 3.0 V to 3.6 V V_{CC} = 4.5 V to 5.5 V	 0 0	 100 20	ns/V
	Input Rise and Fall Time	SC−74A, SC−88A, UDFN6, SOT−553, SOT−953 V_{CC} = 2.0 V V_{CC} = 2.3 V to 2.7 V V_{CC} = 3.0 V to 3.6 V V_{CC} = 4.5 V to 5.5 V	 0 0 0 0	 20 20 10 5	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} (V)	T_A = 25°C			−40°C ≤ T_A ≤ 85°C		−55°C ≤ T_A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V_{T+}	Positive Threshold Voltage		3.0 4.5 5.5	– – –	1.88 2.66 3.21	2.25 3.10 3.70	– – –	2.25 3.10 3.70	– – –	2.25 3.10 3.70	V
V_{T-}	Negative Threshold Voltage		3.0 4.5 5.5	0.65 1.10 1.45	1.03 1.62 2.02	– – –	0.65 1.10 1.45	– – –	0.65 1.10 1.45	– – –	V
V_H	Hysteresis Voltage		3.0 4.5 5.5	0.30 0.40 0.50	0.85 1.05 1.20	1.60 2.00 2.25	0.30 0.40 0.50	1.60 2.00 2.25	0.30 0.40 0.50	1.60 2.00 2.25	V
V_{OL}	Maximum Low−Level Output Voltage	V_{IN} = V_{IH} or V_{IL} I_{OL} = 50 μA	2.0 3.0 4.5	– – –	0.0 0.0 0.0	0.1 0.1 0.1	– – –	0.1 0.1 0.1	– – –	0.1 0.1 0.1	V
		I_{OL} = 4 mA I_{OL} = 8 mA	3.0 4.5	– –	– –	0.36 0.36	– –	0.44 0.44	– –	0.52 0.52	V
I_{IN}	Maximum Input Leakage Current	V_{IN} = 5.5 V or GND	2.0 to 5.5	–	–	±0.1	–	±1.0	–	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	V_{IN} = V_{CC} or GND	5.5	–	–	1.0	–	20	–	40	μA
I_{OFF}	Power Off−Output Leakage Current	V_{OUT} = 5.5 V V_{IN} = 5.5 V	0	–	–	0.25	–	2.5	–	5	μA

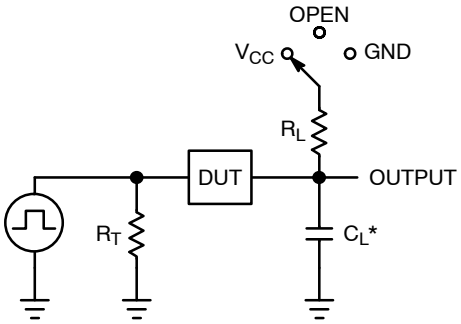
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	V_{CC} (V)	T_A = 25°C			−40°C ≤ T_A ≤ 85°C		−55°C ≤ T_A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{PZL}	Propagation Delay, (A or B) to Y (Figures 3 and 4)	C_L = 15 pF	3.0 to 3.6	–	7.6	11.9	–	14.0	–	16.1	ns
		C_L = 50 pF		–	10.1	15.4	–	17.5	–	19.6	
		C_L = 15 pF	4.5 to 5.5	–	4.9	7.7	–	9.0	–	10.3	
		C_L = 50 pF		–	6.4	9.7	–	11.0	–	12.3	
t_{PLZ}	Propagation Delay, (A or B) to Y (Figures 3 and 4)	C_L = 15 pF	3.0 to 3.6	–	7.6	11.9	–	14.0	–	16.1	ns
		C_L = 50 pF		–	10.1	15.4	–	17.5	–	19.6	
		C_L = 15 pF	4.5 to 5.5	–	4.9	7.7	–	9.0	–	10.3	
		C_L = 50 pF		–	6.4	9.7	–	11.0	–	12.3	
C_{IN}	Maximum Input Capacitance			–	5.0	10	–	10	–	10	pF

		Typical @ 25°C, V_{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Note 5)	16.0	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



C_L includes probe and jig capacitance
R_T is Z_{OUT} of pulse generator (typically 50 Ω)
f = 1 MHz

Test	Switch Position	C_L, pF	R_L, Ω
t_{PLH} / t_{PHL}	Open	See AC Characteristics Table	X
t_{PLZ} / t_{PZL}	V_{CC}		1 k
t_{PHZ} / t_{PZH}	GND		1 k

X = Don't Care

Figure 3. Test Circuit

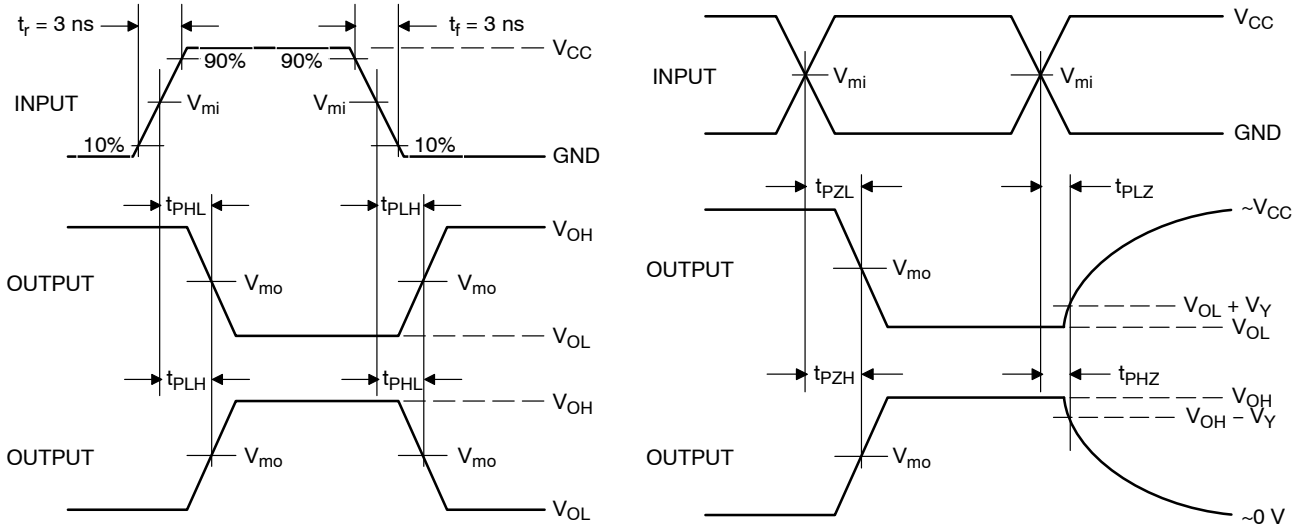


Figure 4. Switching Waveforms

V_{CC}, V	V_{mi}, V	V_{mo}, V		V_Y, V
		t_{PLH}, t_{PHL}	t_{PZL}, t_{PLZ}, t_{PZH}, t_{PHZ}	
3.0 to 3.6	V_{CC}/2	V_{CC}/2	V_{CC}/2	0.3
4.5 to 5.5	V_{CC}/2	V_{CC}/2	V_{CC}/2	0.3

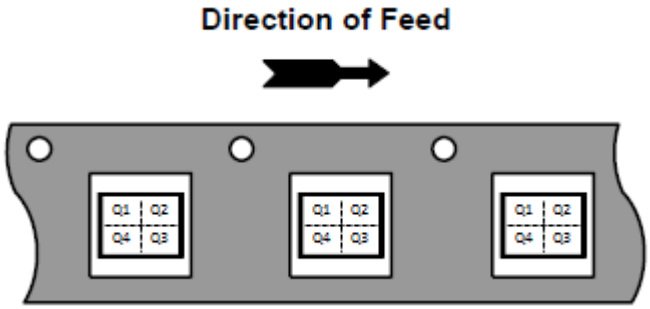
ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping†
M74VHC1G135DFT1G	SC−88A	VZ	Q2	3000 / Tape & Reel
M74VHC1G135DFT2G	SC−88A	VZ	Q4	3000 / Tape & Reel
NLVVHC1G135DFT2G*	SC−88A	VZ	Q4	3000 / Tape & Reel
MC74VHC1G135DBVT1G	SC−74A	VZ	Q4	3000 / Tape & Reel
M74VHC1G135DTT1G	TSOP−5	VZ	Q4	3000 / Tape & Reel
MC74VHC1G135XV5T2G (In Development)	SOT−553	TBD	Q4	4000 / Tape & Reel
MC74VHC1G135P5T5G (In Development)	SOT−953	TBD	Q2	8000 / Tape & Reel
MC74VHC1G135MU1TCG (In Development)	UDFN6, 1.45 x 1.0, 0.5P	TBD	Q4	3000 / Tape & Reel
MC74VHC1G135MU3TCG (In Development)	UDFN6, 1.0 x 1.0, 0.35P	TBD	Q4	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

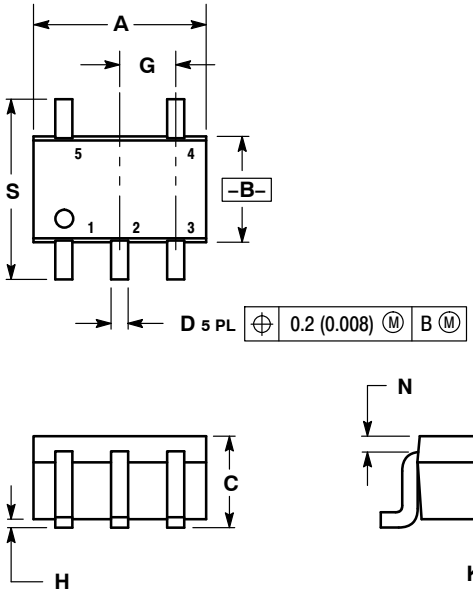
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

Pin 1 Orientation in Tape and Reel



PACKAGE DIMENSIONS

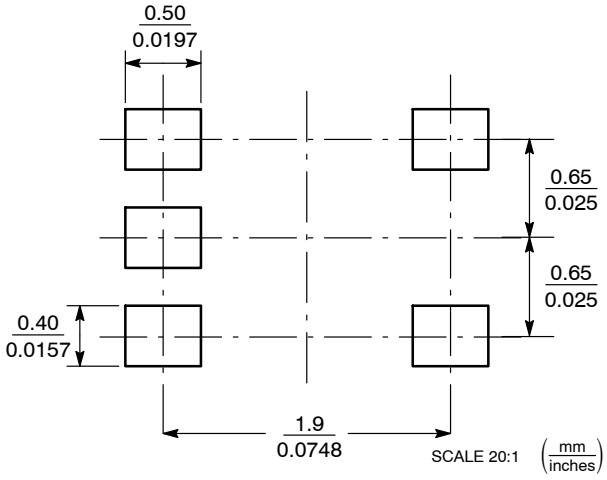
SC−88A (SC−70−5/SOT−353)
CASE 419A−02
ISSUE L



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A−01 OBSOLETE. NEW STANDARD 419A−02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

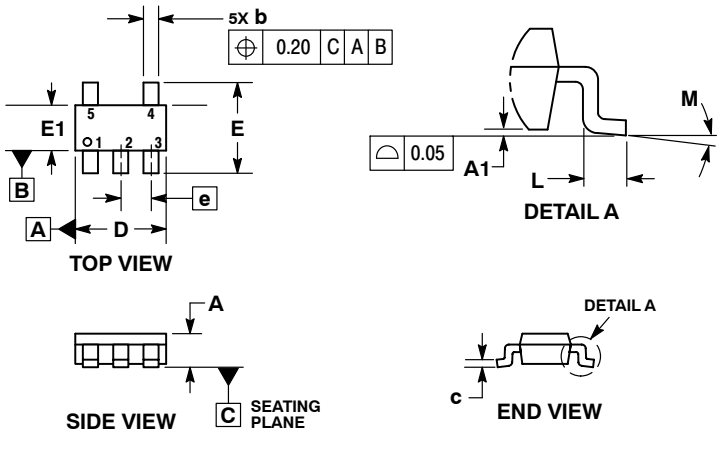
SOLDER FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

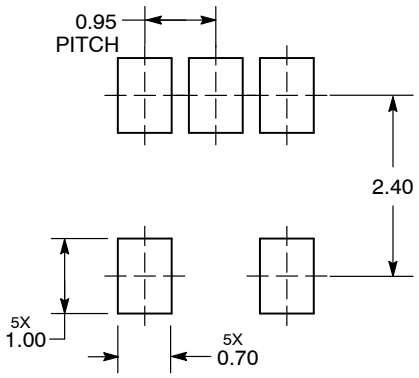
SC−74A
CASE 318BQ
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE.

	MILLIMETERS	
DIM	MIN	MAX
A	0.90	1.10
A1	0.01	0.10
b	0.25	0.50
c	0.10	0.26
D	2.85	3.15
E	2.50	3.00
E1	1.35	1.65
e	0.95 BSC	
L	0.20	0.60
M	0 °	10 °

RECOMMENDED SOLDERING FOOTPRINT*

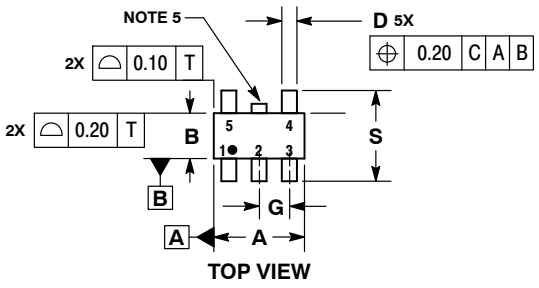


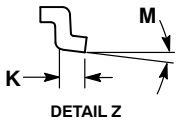
DIMENSIONS: MILLIMETERS

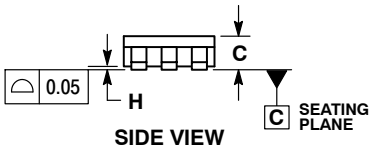
*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

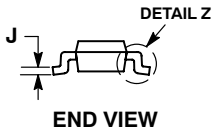
PACKAGE DIMENSIONS

TSOP−5
CASE 483−02
ISSUE M





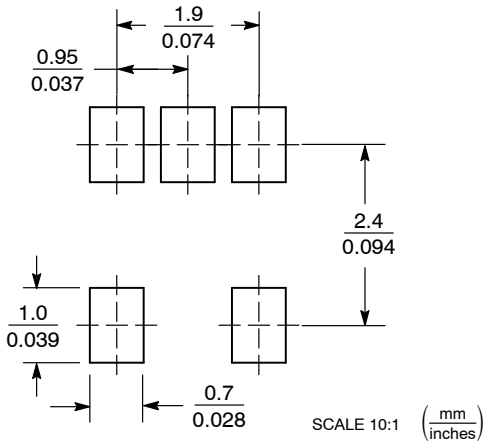




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A.
5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS	
DIM	MIN	MAX
A	2.85	3.15
B	1.35	1.65
C	0.90	1.10
D	0.25	0.50
G	0.95 BSC	
H	0.01	0.10
J	0.10	0.26
K	0.20	0.60
M	0 °	10 °
S	2.50	3.00

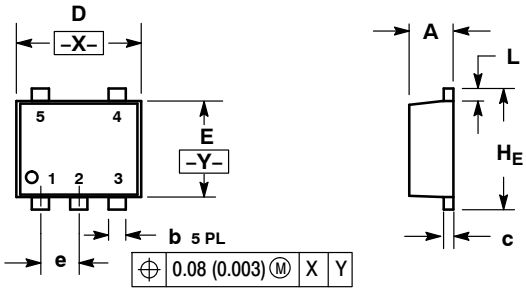
SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

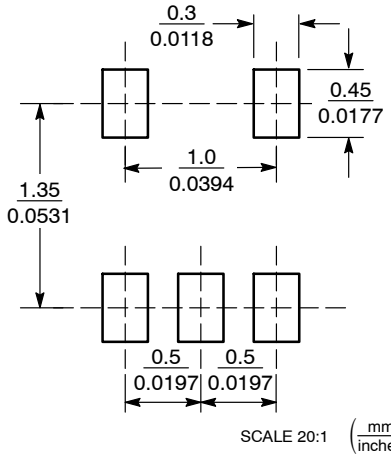
SOT−553, 5 LEAD
CASE 463B
ISSUE C



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.022	0.024
b	0.17	0.22	0.27	0.007	0.009	0.011
c	0.08	0.13	0.18	0.003	0.005	0.007
D	1.55	1.60	1.65	0.061	0.063	0.065
E	1.15	1.20	1.25	0.045	0.047	0.049
e		0.50 BSC			0.020 BSC	
L	0.10	0.20	0.30	0.004	0.008	0.012
H_E	1.55	1.60	1.65	0.061	0.063	0.065

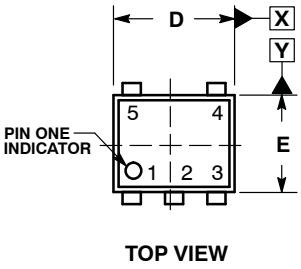
SOLDERING FOOTPRINT*



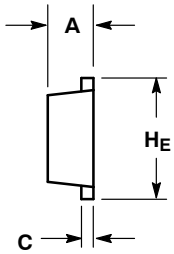
*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

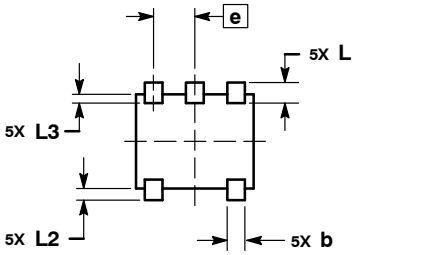
SOT−953
CASE 527AE
ISSUE E



TOP VIEW



SIDE VIEW

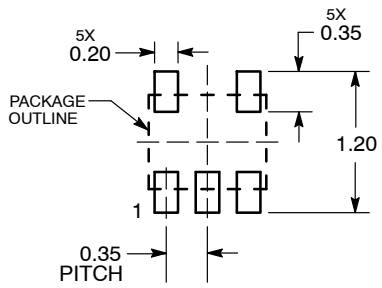


BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.10	0.15	0.20
C	0.07	0.12	0.17
D	0.95	1.00	1.05
E	0.75	0.80	0.85
e	0.35 BSC		
H_E	0.95	1.00	1.05
L	0.175 REF		
L2	0.05	0.10	0.15
L3	---	---	0.15

SOLDERING FOOTPRINT*

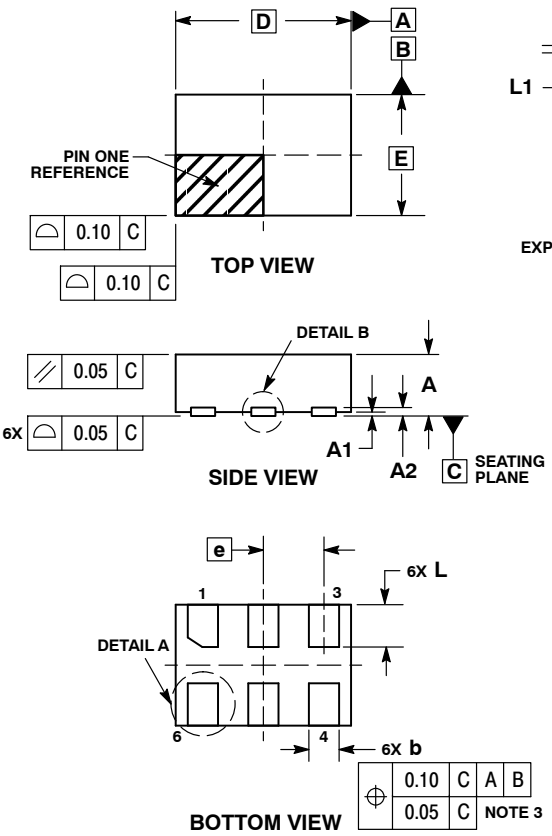


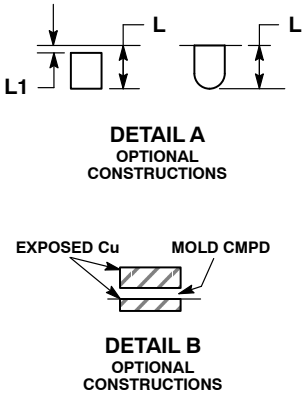
DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

UDFN6, 1.45x1.0, 0.5P
CASE 517AQ
ISSUE O

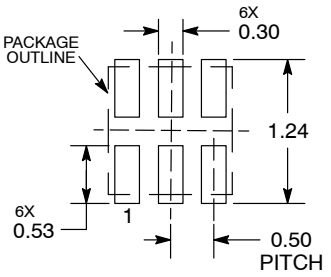




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

	MILLIMETERS	
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A2	0.07 REF	
b	0.20	0.30
D	1.45 BSC	
E	1.00 BSC	
e	0.50 BSC	
L	0.30	0.40
L1	---	0.15

MOUNTING FOOTPRINT

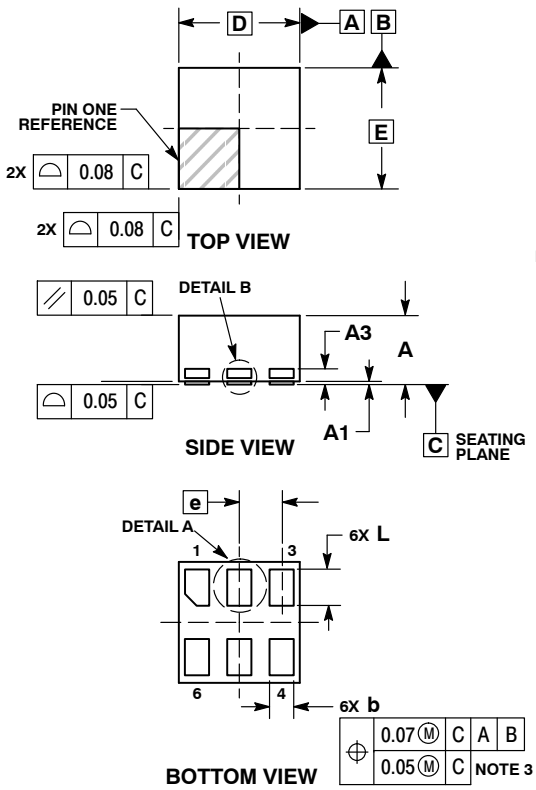


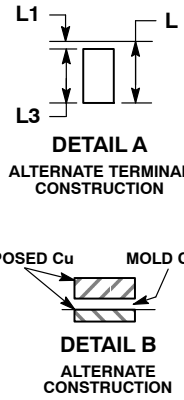
DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

UDFN6, 1x1, 0.35P
CASE 517BX
ISSUE O

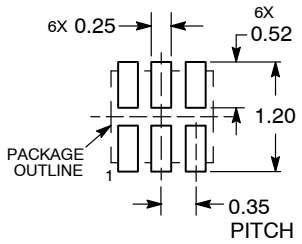




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIMETERS	
DIM	MIN	MAX
A	0.50	0.65
A1	0.00	0.05
A3	0.13 REF	
b	0.17	0.23
D	1.00 BSC	
E	1.00 BSC	
e	0.35	
L	0.20	0.40
L1	---	0.15
L3	0.26	0.33

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSION: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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